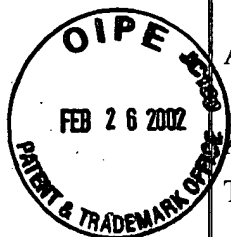


IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



#151B
4-2-02
R. Daler

Applicant(s): Timothy K. Carns, Lee J. DeBruler, John L. Horvath, Michael J. Westphal

Assignee: Zilog, Inc.

Title: PROCESS TO IMPROVE HIGH PERFORMANCE CAPACITOR PROPERTIES IN INTEGRATED MOS TECHNOLOGIES

Serial No.: 09/351,544 / Filing Date: July 12, 1999

Examiner: Brock II, P. Group Art Unit: 2815

Docket No.: M-10889 US (Formerly ZILG.204US0)

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San Francisco, California
February 26, 2002

COMMISSIONER FOR PATENTS
Washington, D. C. 20231

AMENDMENT

Dear Sir:

Responsive to the Official Action mailed on November 11, 2001, applicant responds to the Official Action as follows:

In the Specification:

Please add the following paragraph following the paragraph ending on page 8, line 14, at the end of the "Brief Description of the Drawings" portion:

Figure 12 is a flow chart of the embodiment of the present invention shown in Figures 2-5.

Please replace the paragraph beginning on page 9, line 1, with the following (a marked up version is in the Appendix):

A preferred embodiment of the present invention is shown in Figure 12 and given by the series of steps:

Standard Submicron Core Technology Flow

1. Lower electrode formation
2. Lower electrode doping
3. Lower electrode anneal

B1
B2
LAW OFFICES OF
SKJERVEN MORRILL
MACPHERSON LLP
Three Embarcadero Center
28th Floor
SAN FRANCISCO, CA 94111
(415) 217-6000
FAX (415) 434-0646